1-of-8 Decoder/ Demultiplexer

High-Performance Silicon-Gate CMOS

The MC74HC138A is identical in pinout to the LS138. The device inputs are compatible with standard CMOS outputs; with pullup resistors, they are compatible with LSTTL outputs.

The HC138A decodes a three-bit Address to one-of-eight active-low outputs. This device features three Chip Select inputs, two active-low and one active-high to facilitate the demultiplexing, cascading, and chip-selecting functions. The demultiplexing function is accomplished by using the Address inputs to select the desired device output; one of the Chip Selects is used as a data input while the other Chip Selects are held in their active states.

Features

- Output Drive Capability: 10 LSTTL Loads
- Outputs Directly Interface to CMOS, NMOS and TTL
- Operating Voltage Range: 2.0 to 6.0 V
- Low Input Current: 1.0 μA
- High Noise Immunity Characteristic of CMOS Devices
- In Compliance with the Requirements Defined by JEDEC Standard No. 7A
- Chip Complexity: 100 FETs or 29 Equivalent Gates
- Pb-Free Packages are Available*



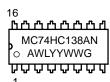
ON Semiconductor®

http://onsemi.com

MARKING DIAGRAMS



PDIP-16 N SUFFIX CASE 648





SOIC-16 D SUFFIX CASE 751B





TSSOP-16 DT SUFFIX CASE 948F





SOEIAJ-16 F SUFFIX CASE 966



A = Assembly Location

L, WL = Wafer Lot
Y, YY = Year
W, WW = Work Week
G = Pb-Free Package
= Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

^{*}For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

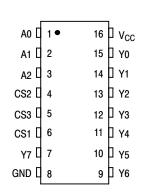


Figure 1. Pin Assignment

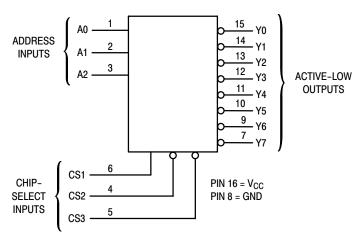


Figure 2. Logic Diagram

FUNCTION TABLE

| | Inputs | | | | Outputs | | | | | | | | |
|-----|--------|-----|-----------|------------|---------|----|------------|----|----|----|----|----|-----------|
| CS1 | CS2 | CS3 | A2 | A 1 | A0 | Y0 | Y 1 | Y2 | Υ3 | Y4 | Y5 | Y6 | Y7 |
| Х | Χ | Н | Χ | Χ | Χ | Н | Н | Н | Н | Н | Н | Н | Н |
| X | Н | Χ | Χ | Χ | Χ | Н | Н | Н | Н | Н | Н | Н | Н |
| L | Χ | Χ | Χ | Χ | Χ | Н | Н | Н | Н | Н | Н | Н | Н |
| Н | L | L | L | L | L | L | Н | Н | Н | Н | Н | Н | Н |
| Н | L | L | L | L | Н | Н | L | Н | Н | Н | Н | Н | Н |
| Н | L | L | L | Η | L | Н | Н | L | Н | Н | Н | Н | Н |
| Н | L | L | L | Н | Н | Н | Н | Η | L | Н | Н | Н | Н |
| Н | L | Г | Н | L | L | Н | Н | Н | Н | L | Н | Н | Н |
| Н | L | L | Н | L | Н | Н | Н | Н | Н | Н | L | Н | Н |
| Н | L | L | Н | Н | L | Н | Н | Н | Н | Н | Н | L | Н |
| Н | L | L | Н | Н | Н | Н | Н | Н | Н | Н | Н | Н | L |

H = high level (steady state); L = Tow level (steady state); X = don't care

ORDERING INFORMATION

| Device | Package | Shipping [†] |
|-----------------|------------------------|-----------------------|
| MC74HC138AN | PDIP-16 | 500 Units / Rail |
| MC74HC138ANG | PDIP-16 (Pb-Free) | 500 Units / Rail |
| MC74HC138AD | SOIC-16 | 48 Units / Rail |
| MC74HC138ADG | SOIC-16 (Pb-Free) | 48 Units / Rail |
| MC74HC138ADR2 | SOIC-16 | 2500 Tape & Reel |
| MC74HC138ADR2G | SOIC-16 (Pb-Free) | 2500 Tape & Reel |
| MC74HC138ADTR2 | TSSOP-16* | 2500 Tape & Reel |
| MC74HC138ADTR2G | TSSOP-16* | 2500 Tape & Reel |
| MC74HC138AF | SOEIAJ-16 | 50 Units / Rail |
| MC74HC138AFG | SOEIAJ-16 (Pb-Free) | 50 Units / Rail |
| MC74HC138AFEL | SOEIAJ-16 | 2000 Tape & Reel |
| MC74HC138AFELG | SOEIAJ-16 (Pb-Free) | 2000 Tape & Reel |

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

^{*}This package is inherently Pb-Free.

MAXIMUM RATINGS

| Symbol | Parameter | Value | Unit |
|------------------|---|--------------------------------|------|
| V _{CC} | DC Supply Voltage (Referenced to GND) | - 0.5 to + 7.0 | V |
| V _{in} | DC Input Voltage (Referenced to GND) | - 0.5 to V _{CC} + 0.5 | V |
| V _{out} | DC Output Voltage (Referenced to GND) | - 0.5 to V _{CC} + 0.5 | V |
| I _{in} | DC Input Current, per Pin | ± 20 | mA |
| l _{out} | DC Output Current, per Pin | ± 25 | mA |
| I _{CC} | DC Supply Current, V _{CC} and GND Pins | ± 50 | mA |
| P _D | Power Dissipation in Still Air, Plastic DIP† SOIC Package† TSSOP Package† | 750 500 450 | mW |
| T _{stg} | Storage Temperature | - 65 to + 150 | °C |
| T _L | Lead Temperature, 1 mm from Case for 10 Seconds (Plastic DIP, SOIC or TSSOP Package) | 260 | °C |

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high-impedance circuit. For proper operation, Vin and Vout should be constrained to the range GND \leq (V_{in} or V_{out}) \leq V_{CC}.

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or V_{CC}). Unused outputs must be left open.

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected. †Derating – Plastic DIP: – 10 mW/°C from 65° to 125°C

SOIC Package: - 7 mW/°C from 65° to 125°C

TSSOP Package: - 6.1 .W/°C from 65° to 125°C

For high frequency or heavy load considerations, see Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

RECOMMENDED OPERATING CONDITIONS

| Symbol | Parameter | Min | Max | Unit |
|------------------------------------|--|------|--------------------|------|
| V _{CC} | DC Supply Voltage (Referenced to GND) | 2.0 | 6.0 | V |
| V _{in} , V _{out} | DC Input Voltage, Output Voltage (Referenced to GND) | 0 | V _{CC} | V |
| T _A | Operating Temperature, All Package Types | - 55 | + 125 | °C |
| t _r , t _f | Input Rise and Fall Time $V_{CC} = 2.0 \text{ V}$ (Figure 2) $V_{CC} = 4.5 \text{ V}$ $V_{CC} = 6.0 \text{ V}$ | 0 | 1000 500 400 | ns |

DC ELECTRICAL CHARACTERISTICS (Voltages Referenced to GND)

| | | | V _{CC} | Guara | nteed Limit | t | |
|-----------------|--------------------------------------|--|--------------------------|---------------------------|---------------------------|---------------------------|------|
| Symbol | Parameter | Test Conditions | ٧ | –55°C to 25°C | ≤ 85°C | ≤ 125°C | Unit |
| V _{IH} | Minimum High-Level Input Voltage | $V_{out} = 0.1 \text{ V or } V_{CC} - 0.1 \text{ V}$ $ I_{out} \le 20 \mu\text{A}$ | 2.0 3.0 4.5 6.0 | 1.5 2.1 3.15 4.2 | 1.5 2.1 3.15 4.2 | 1.5 2.1 3.15 4.2 | V |
| V _{IL} | Maximum Low–Level Input Voltage | $V_{out} = 0.1 \text{ V or } V_{CC} - 0.1 \text{ V}$ $ I_{out} \le 20 \mu\text{A}$ | 2.0 3.0 4.5 6.0 | 0.5 0.9 1.35 1.8 | 0.5 0.9 1.35 1.8 | 0.5 0.9 1.35 1.8 | V |
| V _{OH} | Minimum High-Level Output Voltage | $V_{in} = V_{IH} \text{ or } V_{IL}$ $ I_{out} \le 20 \mu\text{A}$ | 2.0 4.5 6.0 | 1.9 4.4 5.9 | 1.9 4.4 5.9 | 1.9 4.4 5.9 | V |
| | | $\begin{split} V_{\text{in}} = V_{\text{IH}} \text{ or } V_{\text{IL}} & \mid I_{\text{out}} \mid \leq 2.4 \text{ mA} \\ & \mid I_{\text{out}} \mid \leq 4.0 \text{ mA} \\ & \mid I_{\text{out}} \mid \leq 5.2 \text{ mA} \end{split}$ | 3.0 4.5 6.0 | 2.48 3.98 5.48 | 2.34 3.84 5.34 | 2.20 3.70 5.20 | |

| V _{OL} | Maximum Low–Level Output Voltage | $V_{in} = V_{IH} \text{ or } V_{IL}$ $ I_{out} \le 20 \ \mu\text{A}$ | 2.0 4.5 6.0 | 0.1 0.1 0.1 | 0.1 0.1 0.1 | 0.1 0.1 0.1 | V |
|-----------------|---|--|-------------------|----------------------|----------------------|----------------------|----|
| | | $V_{\text{in}} = V_{\text{IH}} \text{ or } V_{\text{IL}} \mid I_{\text{out}} \mid \leq 2.4 \text{ mA}$ $\mid I_{\text{out}} \mid \leq 4.0 \text{ mA}$ $\mid I_{\text{out}} \mid \leq 5.2 \text{ mA}$ | 3.0 4.5 6.0 | 0.26 0.26 0.26 | 0.33 0.33 0.33 | 0.40 0.40 0.40 | |
| l _{in} | Maximum Input Leakage Current | $V_{in} = V_{CC}$ or GND | 6.0 | ± 0.1 | ± 1.0 | ± 1.0 | μΑ |
| Icc | Maximum Quiescent Supply Current (per Package) | $V_{in} = V_{CC}$ or GND $I_{out} = 0 \mu A$ | 6.0 | 4 | 40 | 160 | μΑ |

NOTE:Information on typical parametric values can be found in Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

AC ELECTRICAL CHARACTERISTICS (C $_L$ = 50 pF, Input t_{r} = t_{f} = 6.0 ns)

| | | V _{CC} | Guara | nteed Limit | | |
|--|---|--------------------------|-----------------------|------------------------|------------------------|------|
| Symbol | Parameter | V | -55°C to 25°C | ≤ 85°C | ≤ 125°C | Unit |
| t _{PLH} , t _{PHL} | Maximum Propagation Delay, Input A to Output Y (Figures 1 and 4) | 2.0 3.0 4.5 6.0 | 135 90 27 23 | 170 125 34 29 | 205 165 41 35 | ns |
| t _{PLH} , t _{PHL} | Maximum Propagation Delay, CS1 to Output Y (Figures 2 and 4) | 2.0 3.0 4.5 6.0 | 110 85 22 19 | 140 100 28 24 | 165 125 33 28 | ns |
| t _{PLH} , t _{PHL} | Maximum Propagation Delay, CS2 or CS3 to Output Y (Figures 3 and 4) | 2.0 3.0 4.5 6.0 | 120 90 24 20 | 150 120 30 26 | 180 150 36 31 | ns |
| t _{TLH} , t _{THL} | Maximum Output Transition Time, Any Output (Figures 2 and 4) | 2.0 3.0 4.5 6.0 | 75 30 15 13 | 95 40 19 16 | 110 55 22 19 | ns |
| C _{in} | Maximum Input Capacitance | _ | 10 | 10 | 10 | pF |

NOTE: For propagation delays with loads other than 50 pF, and information on typical parametric values, see Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

| | | Typical @ 25°C, V _{CC} = 5.0 V | |
|----------|--|---|----|
| C_{PD} | Power Dissipation Capacitance (Per Package)* | 55 | pF |

^{*}Used to determine the no–load dynamic power consumption: P_D = C_{PD} V_{CC}²f + I_{CC} V_{CC}. For load considerations, see Chapter 2 of the ON Semiconductor High–Speed CMOS Data Book (DL129/D).

SWITCHING WAVEFORMS

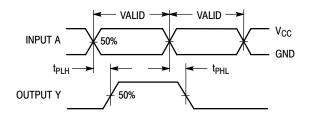


Figure 1.

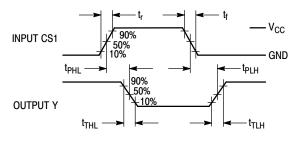


Figure 2.

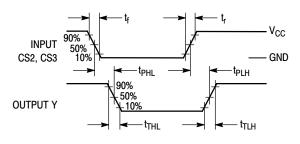
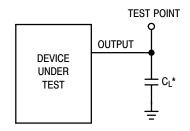


Figure 3.



*Includes all probe and jig capacitance

Figure 4. Test Circuit

PIN DESCRIPTIONS

ADDRESS INPUTS A0, A1, A2 (Pins 1, 2, 3)

Address inputs. These inputs, when the chip is selected, determine which of the eight outputs is active—low.

CONTROL INPUTS CS1, CS2, CS3 (Pins 6, 4, 5)

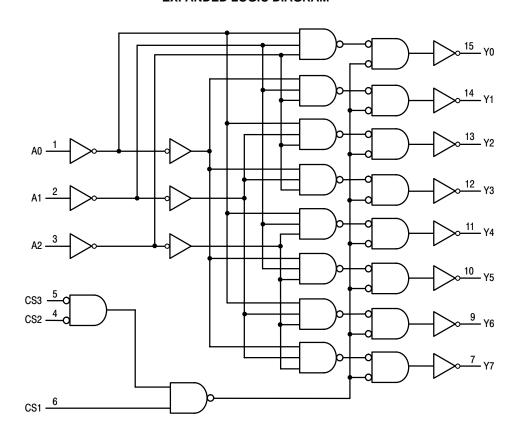
Chip select inputs. For CS1 at a high level and CS2, CS3 at a low level, the chip is selected and the outputs follow the

Address inputs. For any other combination of CS1, CS2, and CS3, the outputs are at a logic high.

OUTPUTS Y0 - Y7 (Pins 15, 14, 13, 12, 11, 10, 9, 7)

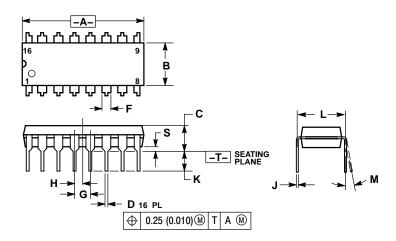
Active—low Decoded outputs. These outputs assume a low level when addressed and the chip is selected. These outputs remain high when not addressed or the chip is not selected.

EXPANDED LOGIC DIAGRAM



PACKAGE DIMENSIONS

PDIP-16 **N SUFFIX** CASE 648-08 **ISSUE T**

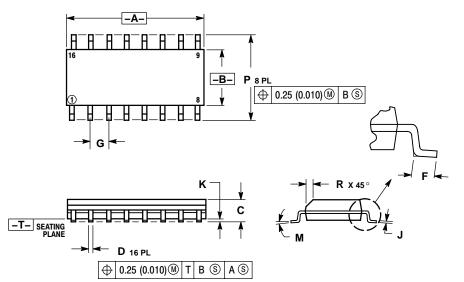


NOTES:

- DIMENSIONING AND TOLERANCING PER
- Inimensioning and Tolerancing F ANSI Y14.5M, 1982.
 CONTROLLING DIMENSION: INCH.
 IDIMENSION L TO CENTER OF LEADS WHEN FORMED PARALLEL.
 DIMENSION B DOES NOT INCLUDE MOLD FLASH.
- 5. ROUNDED CORNERS OPTIONAL.

| | INC | HES | MILLIN | IETERS | |
|-----|-------|-------|----------|--------|--|
| DIM | MIN | MAX | MIN | MAX | |
| Α | 0.740 | 0.770 | 18.80 | 19.55 | |
| В | 0.250 | 0.270 | 6.35 | 6.85 | |
| С | 0.145 | 0.175 | 3.69 | 4.44 | |
| D | 0.015 | 0.021 | 0.39 | 0.53 | |
| F | 0.040 | 0.70 | 1.02 | 1.77 | |
| G | 0.100 | BSC | 2.54 BSC | | |
| Н | 0.050 | BSC | 1.27 BSC | | |
| J | 0.008 | 0.015 | 0.21 | 0.38 | |
| K | 0.110 | 0.130 | 2.80 | 3.30 | |
| L | 0.295 | 0.305 | 7.50 | 7.74 | |
| М | 0° | 10 ° | 0 ° | 10 ° | |
| S | 0.020 | 0.040 | 0.51 | 1.01 | |

SOIC-16 **D SUFFIX** CASE 751B-05 **ISSUE J**



- NOTES:

 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

 2. CONTROLLING DIMENSION: MILLIMETER.

 3. DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION.

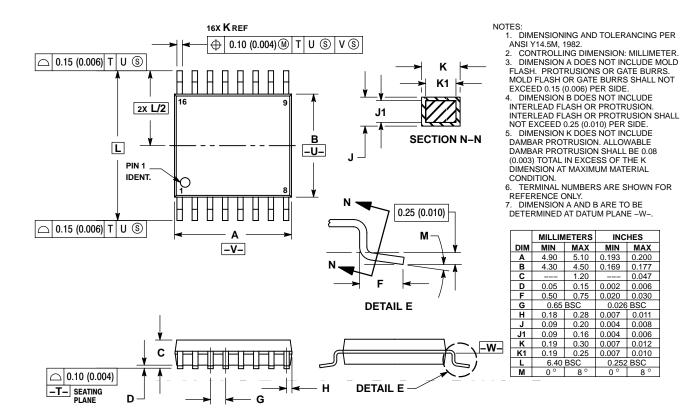
 4. MAXIMUM MOLD PROTRUSION 0.15 (0.006) DED SIGN.

- MAXIMUM MOLD PHOLICISION 0.15 (0.006)
 PER SIDE.
 DIMENSION D DOES NOT INCLUDE DAMBAR
 PROTRUSION. ALLOWABLE DAMBAR
 PROTRUSION SHALL BE 0.127 (0.005) TOTAL
 IN EXCESS OF THE D DIMENSION AT
 MAXIMUM MATERIAL CONDITION.

| | MILLIN | IETERS | INCHES | | |
|-----|--------|--------|-----------|-------|--|
| DIM | MIN | MAX | MIN | MAX | |
| Α | 9.80 | 10.00 | 0.386 | 0.393 | |
| В | 3.80 | 4.00 | 0.150 | 0.157 | |
| С | 1.35 | 1.75 | 0.054 | 0.068 | |
| D | 0.35 | 0.49 | 0.014 | 0.019 | |
| F | 0.40 | 1.25 | 0.016 | 0.049 | |
| G | 1.27 | BSC | 0.050 BSC | | |
| J | 0.19 | 0.25 | 0.008 | 0.009 | |
| K | 0.10 | 0.25 | 0.004 | 0.009 | |
| M | 0° | 7° | 0° | 7° | |
| P | 5.80 | 6.20 | 0.229 | 0.244 | |
| R | 0.25 | 0.50 | 0.010 | 0.019 | |

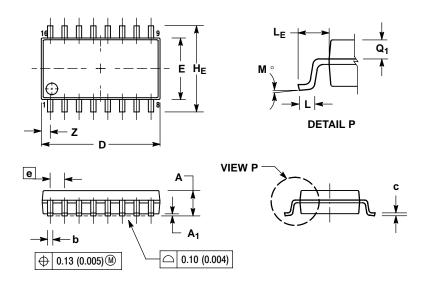
PACKAGE DIMENSIONS

TSSOP-16 DT SUFFIX CASE 948F-01 ISSUE A



PACKAGE DIMENSIONS

SOEIAJ-16 **F SUFFIX** CASE 966-01 **ISSUE O**



NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI DIMENSIONING AND TOLERANCING PER A Y14.5M, 1982.
 CONTROLLING DIMENSION: MILLIMETER.
- 2. CONTROLLING DIMENSION. MILLIMITER.
 3. DIMENSIONS D AND E DO NOT INCLUDE
 MOLD FLASH OR PROTRUSIONS AND ARE
 MEASURED AT THE PARTING LINE. MOLD FLASH
 OR PROTRUSIONS SHALL NOT EXCEED 0.15
- OR PROTRUSIONS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.

 4. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.

 5. THE LEAD WIDTH DIMENSION (b) DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE LEAD WIDTH DIMENSION AT MAXIMUM MATERIAL CONDITION. DAMBAR CANNOT BE LOCATED ON THE LOWER RADILIS OR THE FOOT MINIMIM SPACE RADIUS OR THE FOOT. MINIMUM SPACE BETWEEN PROTRUSIONS AND ADJACENT LEAD TO BE 0.46 (0.018).

| | MILLIN | IETERS | INC | HES | |
|----------------|--------|--------|-----------|-------|--|
| DIM | MIN | MAX | MIN | MAX | |
| Α | | 2.05 | | 0.081 | |
| A ₁ | 0.05 | 0.20 | 0.002 | 0.008 | |
| b | 0.35 | 0.50 | 0.014 | 0.020 | |
| С | 0.18 | 0.27 | 0.007 | 0.011 | |
| D | 9.90 | 10.50 | 0.390 | 0.413 | |
| E | 5.10 | 5.45 | 0.201 | 0.215 | |
| е | 1.27 | BSC | 0.050 BSC | | |
| HE | 7.40 | 8.20 | 0.291 | 0.323 | |
| L | 0.50 | 0.85 | 0.020 | 0.033 | |
| LE | 1.10 | 1.50 | 0.043 | 0.059 | |
| M | 0 ° | 10° | 0 ° | 10° | |
| Q ₁ | 0.70 | 0.90 | 0.028 | 0.035 | |
| 7 | | 0.78 | | 0.031 | |

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